74LVTH652 Low Voltage Octal Transceiver/Register with 3-STATE Outputs

FAIRCHILD

SEMICONDUCTOR

74LVTH652 Low Voltage Octal Transceiver/Register with 3-STATE Outputs

General Description

The LVTH652 consists of bus transceiver circuits with Dtype flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the input bus or from the internal registers. Data on the A or B bus will be clocked into the registers as the appropriate clock <u>pin goes</u> to HIGH logic level. Output Enable pins (OEAB, <u>OEBA</u>) are provided to control the transceiver function. (See Functional Description).

The LVTH652 data inputs include bushold, eliminating the need for external pull-up resistors to hold unused inputs.

This octal transceiver/register is designed for low-voltage (3.3V) V_{CC} applications, but with the capability to provide a TTL interface to a 5V environment. The LVTH652 is fabricated with an advanced BiCMOS technology to achieve high speed operation similar to 5V ABT while maintaining low power dissipation.

Features

- Input and output interface capability to systems at 5V $\rm V_{CC}$
- Bushold data inputs eliminate the need for external pullup resistors to hold unused inputs
- Live insertion/extraction permitted
- Power Up/Down high impedance provides glitch-free bus loading
- Outputs source/sink –32 mA/+64 mA
- Functionally compatible with the 74 series 652
- Latch-up performance exceeds 500 mA

Ordering Code:

Order Number	Package Number	Package Description
74LVTH652WM	M24B	24-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-013, 0.300" Wide
74LVTH652MTC	MTC24	24-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide

Devices also available in Tape and Reel. Specify by appending suffix letter "X" to the ordering code.

Logic Symbols IEEE/IEC 11111 OFBA EN1 (BA) OEAB EN2 (AB) PAR OEAI СРВА G4 AB SBA G5 OEBA СРАВ G6 SAF G7 B_a B₃ B₄ B 86 B-≥1Þ

Pin Descriptions

Pin Names	Description
A ₀ -A ₇	Data Register A Inputs/
	3-STATE Outputs
В ₀ –В ₇	Data Register B Inputs/
	3-STATE Outputs
CPAB, CPBA	Clock Pulse Inputs
SAB, SBA	Select Inputs
OEAB, OEBA	Output Enable Inputs

Connection Diagram CPAB 24 $v_{\rm CC}$ SAB 23 - СРВА - SBA OEAB · 22 - OEBA 21 A₀ 20 A_1 - В_О 19 Α2 - B₁ Α3 18 • В₂ Α4 B₃ 16 Β4 A, 15 B₅ A₆

14 - B₆ 13 - B₇

Α-

GND - 12

Truth Table

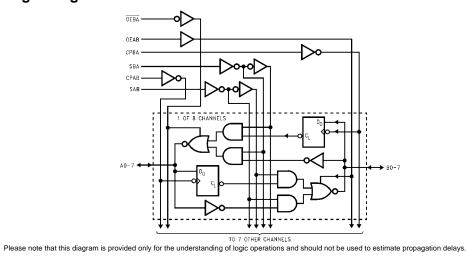
(Note 1)

Inputs						Inputs/	Outputs	On creating a Marcia
OEAB	OEBA	CPAB	СРВА	SAB	SBA	A ₀ thru A ₇	B ₀ thru B ₇	Operating Mode
L	Н	H or L	H or L	Х	Х	Input	Input	Isolation
L	Н	~	~	Х	Х			Store A and B Data
Х	Н	~	H or L	Х	Х	Input	Not Specified	Store A, Hold B
Н	Н	~	<u>`</u>	Х	Х	Input	Output	Store A in Both Registers
L	Х	H or L	~	Х	Х	Not Specified	Input	Hold A, Store B
L	L	~	~	Х	Х	Output	Input	Store B in Both Registers
L	L	Х	Х	Х	L	Output	Input	Real-Time B Data to A Bus
L	L	Х	H or L	Х	Н			Store B Data to A Bus
Н	Н	Х	Х	L	Х	Input	Output	Real-Time A Data to B Bus
Н	Н	H or L	Х	Н	Х			Stored A Data to B Bus
Н	L	H or L	H or L	Н	Н	Output	Output	Stored A Data to B Bus and Stored B Data to A Bus

H = HIGH Voltage Level L = LOW Voltage Level X = Immaterial \checkmark = LOW to HIGH Clock Transition

Note 1: The data output functions may be enabled or disabled by various signals at OEAB or OEBA inputs. Data input functions are always enabled, i.e., data at the bus pins will be stored on every LOW-to-HIGH transition on the clock inputs.

Logic Diagram



Functional Description

OEAB

L

OEAB

Х

L

L

In the transceiver mode, data present at the HIGH impedance port may be stored in either the A or B register or both.

The select (SAB, SBA) controls can multiplex stored and real-time.

The examples below demonstrate the four fundamental bus-management functions that can be performed with the LVTH652.

Data on the A or B data bus, or both can be stored in the internal D-type flip-flop by LOW-to-HIGH transitions at the appropriate Clock Inputs (CPAB, CPBA) regardless of the Select or Output Enable Inputs. When SAB and SBA are in the real time transfer mode, it is also possible to store data without using the internal D-type flip-flops by simultaneously enabling OEAB and OEBA. In this configuration each Output reinforces its Input. Thus when all other data sources to the two sets of bus lines are in a HIGH impedance state, each set of bus lines will remain at its last state.

Real-Time Transfer Real-Time Transfer Bus B to Bus A Bus A to Bus B ž OEBA OEAB CPAB СРВА SAB OEBA CPAB СРВА SAB SBA н н Х Х L L Х Х Х L Transfer Storage Data to A or B Storage Sile $\underline{\circ}$ BUS E OEBA CPAB СРВА SAB SBA OEAB OEBA CPAB CPBA SAB н Х Х Х н L H or L H or L н ~ Х Х ~ Х Х н ~ ~ Х Х

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SBA

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SBA

Х

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Absolute Maximum Ratings

Symbol	Parameter	Value	Conditions	Units	
′cc	Supply Voltage	-0.5 to +4.6		V	
/1	DC Input Voltage	-0.5 to +7.0		V	
/ ₀	DC Output Voltage	-0.5 to +7.0	Output in 3-STATE	V	
		-0.5 to +7.0	Output in HIGH or LOW State (Note 3)	v	
IK	DC Input Diode Current	-50	V _I < GND	mA	
ОК	DC Output Diode Current	-50	V _O < GND	mA	
0	DC Output Current	64	V _O > V _{CC} Output at HIGH State	mA	
		128	V _O > V _{CC} Output at LOW State	IIIA	
сс	DC Supply Current per Supply Pin	±64		mA	
GND	DC Ground Current per Ground Pin	±128		mA	
T _{STG}	Storage Temperature	-65 to +150		°C	

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Units
V _{CC}	Supply Voltage	2.7	3.6	V
VI	Input Voltage	0	5.5	V
I _{OH}	HIGH Level Output Current		-32	mA
I _{OL}	LOW Level Output Current		64	mA
T _A	Free-Air Operating Temperature	-40	85	°C
$\Delta t/\Delta V$	Input Edge Rate, V _{IN} = 0.8V–2.0V, V _{CC} = 3.0V	0	10	ns/V

Note 2: Absolute Maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum rated conditions is not implied. Note 3: I_{O} Absolute Maximum Rating must be observed.

			V _{CC}	T _A =-40°C to +85°C			
Symbol	Parameter	(V)	Min	Max	Units	Conditions	
V _{IK}	Input Clamp Diode Voltage		2.7		-1.2	V	I _I = -18 mA
VIH	Input HIGH Voltage		2.7-3.6	2.0		V	$V_0 \le 0.1V$ or
V _{IL}	Input LOW Voltage		2.7-3.6		0.8	v	$V_{O} \ge V_{CC} - 0.1V$
V _{OH}	Output HIGH Voltage		2.7–3.6	V _{CC} - 0.2		V	I _{OH} = -100 μA
			2.7	2.4		V	I _{OH} = -8 mA
			3.0	2.0		V	I _{OH} = -32 mA
V _{OL}	Output LOW Voltage		2.7		0.2	V	I _{OL} = 100 μA
			2.7		0.5	V	I _{OL} = 24 mA
			3.0		0.4	V	I _{OL} = 16 mA
			3.0		0.5	V	I _{OL} = 32 mA
		3.0		0.55	V	I _{OL} = 64 mA	
I _{I(HOLD)}	Bushold Input Minimum Drive	Bushold Input Minimum Drive		75		μA	V _I = 0.8V
				-75		μA	V _I = 2.0V
I _{I(OD)}	Bushold Input Over-Drive Current to Change State		3.0	500		μA	(Note 4)
				-500		μA	(Note 5)
lj –	Input Current		3.6		10	μA	V _I = 5.5V
	Γ	Control Pins	3.6		±1	μA	$V_I = 0V \text{ or } V_{CC}$
		Data Pins	3.6		-5	μA	$V_I = 0V$
					1	μA	$V_I = V_{CC}$
I _{OFF}	Power OFF Leakage Current		0		±100	μA	$0V \le V_1 \text{ or } V_0 \le 5.5V$
I _{PU/PD}	Power Up/Down 3-STATE Output Current		0–1.5V		±100	μΑ	$V_O = 0.5V$ to 3.0V $V_I = GND$ or V_{CC}
I _{OZL}	3-STATE Output Leakage Curren	nt	3.6		-5	μA	V _O = 0.0V
I _{OZH}	3-STATE Output Leakage Curren	nt	3.6		5	μA	V _O = 3.6V
I _{OZH} +	3-STATE Output Leakage Curren	nt	3.6		10	μA	$V_{CC} < V_O \le 5.5V$
ICCH	Power Supply Current		3.6		0.19	mA	Outputs HIGH
I _{CCL}	Power Supply Current		3.6		5	mA	A or B Port Outputs LOW
I _{CCZ}	Power Supply Current		3.6		0.19	mA	Outputs Disabled
I _{CCZ} +	Power Supply Current		3.6		0.19	mA	$V_{CC} \le V_O \le 5.5V$
							Outputs Disabled
ΔI_{CC}	Increase in Power Supply Curren (Note 6)	nt	3.6		0.2	mA	One Input at V _{CC} – 0.6V Other Inputs at V _{CC} or GND

Note 4: An external driver must source at least the specified current to switch from LOW-to-HIGH.

Note 5: An external driver must sink at least the specified current to switch from HIGH-to-LOW.

Note 6: This is the increase in supply current for each input that is at the specified voltage level rather than V_{CC} or GND.

Dynamic Switching Characteristics (Note 7)

Symbol	Parameter	V_{CC} $T_A = 25^{\circ}C$				Units	Conditions	
Symbol	Falaneter	(V)	Min	Тур	Max	Units	$\textbf{C}_{\textbf{L}}=\textbf{50}~\textbf{pF},~\textbf{R}_{\textbf{L}}=\textbf{500}\Omega$	
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	3.3		0.8		V	(Note 8)	
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	3.3		-0.8		V	(Note 8)	

Note 7: Characterized in SOIC package. Guaranteed parameter, but not tested.

Note 8: Max number of outputs defined as (n). n-1 data inputs are driven 0V to 3V. Output under test held LOW.

74LVTH652

AC Electrical Characteristics

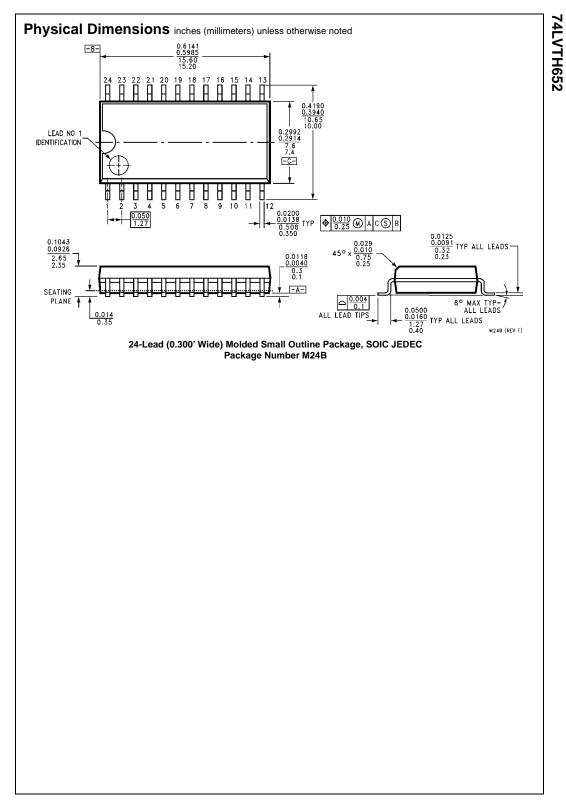
			$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$					
Symbol	Parameter		Units					
Cymbol	i aranicter	V _{CC} = 3.	$3V \pm 0.3V$	$V_{CC} = 2.7V$				
		Min	Max	Min	Max	1		
f _{MAX}	Maximum Clock Frequency	150		150		MHz		
t _{PLH}	Propagation Delay Data to Output	1.8	5.6	1.8	6.2			
t _{PHL}	Clock to A or B	1.8	4.8	1.8	5.6	ns		
t _{PLH}	Propagation Delay Data to Output	1.3	4.5	1.3	4.9	ns		
t _{PHL}	Data to A or B	1.3	4.6	1.3	5.2	115		
t _{PLH}	Propagation Delay Data to Output	1.5	5.5	1.5	6.4	ns		
t _{PHL}	SBA or SAB to A or B	1.5	5.4	1.5	6.1	115		
t _{PZH}	Output Enable Time	1.1	5.2	1.1	6.5			
t _{PZL}	OE to A	1.1	5.6	1.1	6.6	ns		
t _{PHZ}	Output Disable Time	2.0	5.5	2.0	6.1			
t _{PLZ}	OE to A	2.0	5.5	2.0	5.9	ns		
t _{PZH}	Output Enable Time	1.3	4.9	1.3	5.7			
t _{PZL}	OE to B	1.3	5.3	1.3	5.8	ns		
t _{PHZ}	Output Disable Time	1.5	5.6	1.5	6.7			
t _{PLZ}	OE to B	1.5	5.6	1.5	6.3	ns		
t _W	Pulse Duration Clock HIGH or LOW	3.3		3.3		ns		
ts	Setup Time Data HIGH before CP	1.2		1.5				
	Data LOW before CP	1.6		2.2		ns		
t _H	Hold Time Data HIGH or LOW after CP	0.8		0.8		ns		
t _{OSHL}	Output to Output Skew	1	1.0		1.0			
tOSLH	(Note 9)		1.0		1.0	ns		

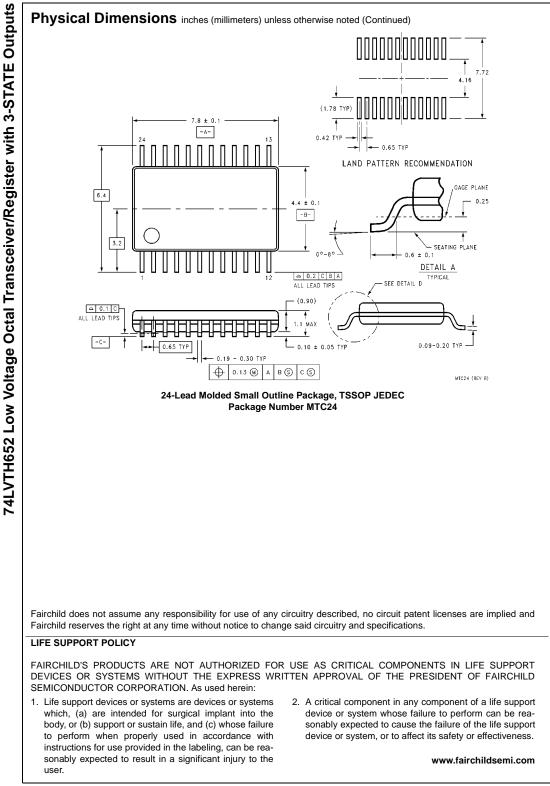
Note 9: Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}).

Capacitance (Note 10)

Symbol	Parameter	Conditions	Typical	Units
CIN	Input Capacitance	$V_{CC} = 0V, V_I = 0V \text{ or } V_{CC}$	4	pF
C _{I/O}	Input/Output Capacitance	$V_{CC} = 3.0V, V_O = 0V \text{ or } V_{CC}$	8	pF
Nata 10: Co	negitenes is measured at frequency f 1 MUz, part	MIL CTD 000D Method 2010		

Note 10: Capacitance is measured at frequency f = 1 MHz, per MIL-STD-883B, Method 3012.





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8